Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and (ultraviolet adj (radiat$6 or irradiat$6))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:13
L2	36	semiconductor and (grind$4 near5 back) and (plasma adj (etch$6 or lift-off)) and radiat$6 and adhesive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:22
L3	3	semiconductor and (grind$4 near5 back) and (plasma adj (etch$6 or lift-off)) and radiat$6 and adhesive and (ultraviolet adj (radiat$6 or irradiat$6))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:21
L4	1	semiconductor and (grind$4 near5 back) and (plasma adj (etch$6 or lift-off)) and radiat$6 and adhesive and (ultraviolet adj (radiat$6 or irradiat$6)) and @ad<="20030213"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:20
L5	3	semiconductor and (grind$4 adj10 back) and (plasma adj (etch$6 or lift-off)) and radiat$6 and adhesive and (ultraviolet adj (radiat$6 or irradiat$6))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:21
S1	364324	semiconductor and (dual adj damascene) and (mask or resist or photoresist) transfer$6 and pattern$5 and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 14:14
S2	998	semiconductor and (dual adj damascene) and (mask or resist or photoresist) and transfer$6 and pattern$5 and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 14:15
S3	13	semiconductor and (dual adj damascene) and (mask or resist or photoresist) and transfer$6 and pattern$5 and (light adj transmi$9) and (light adj shield$6) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/22 15:03

S4	994	semiconductor and (mask or resist or photoresist) and transfer$6 and pattern$5 and (light adj transmi$9) and (light adj shield$6) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/30 07:53
S5	2	438/637,638,639,640.ccls. and (mask or resist or photoresist) and transfer$6 and pattern$5 and (light adj transmi$9) and (light adj shield$6) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 14:20
S6	13	semiconductor and (mask or resist or photoresist) and transfer$6 and pattern$5 and (light adj transmi$9) and (light adj shield$6) and (dual adj damascene) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 14:41
S7	5491	dual adj damascene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 08:30
S8	5353	(dual adj damascene) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/22 11:58
S9	4815	(dual adj damascene) and @ad<="20030522" and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/30 12:41
S10	3286	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 14:13
S11	35	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj transmi$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:17
S12	46	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj (transmi$9 or shield$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:18
S13	9	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj transmi$9) and (light adj shield$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/30 12:44

S14	1851	(438/637).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/30 12:40
S15	633	(438/638).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/30 12:40
S16	501	(438/639).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/30 12:40
S17	391	(438/640).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/30 12:40
S18	5	438/637,638,639,640.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj transmi$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 14:19
S19	1	438/637,638,639,640.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj transmi$9) and (light adj shield$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/30 12:44
S20	19	"438"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj transmi$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/30 12:48
S21	2	(("6656644") or ("6596656")).PN.	USPAT; USOCR	OR	OFF	2004/11/23 08:27
S22	1	("6656644").PN.	USPAT; USOCR	OR	OFF	2005/06/27 11:28
S25	13	semiconductor and (dual adj damascene) and (mask or resist or photoresist) and transfer$6 and pattern$5 and (light adj transmi$9) and (light adj shield$6) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 15:00

S26	1010	semiconductor and (mask or resist or photoresist) and transfer$6 and pattern$5 and (light adj transmi$9) and (light adj shield$6) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/30 08:54
S30	152	((((mask or resist or photoresist) adj pattern$6) with (light adj transmi$9) with (light adj shield$6)) and @ad<="20030522"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/30 09:00
S31	104	S30 and (hole or via or groove or trench or open$5 or aperture)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/30 09:01
S32	49	(("6140226") or ("6096655") or ("5877076") or ("5882996") or ("5935762") or ("6323118") or ("6433381") or ("6448176") or ("6498089") or ("6395456") or ("6020255") or ("6194128") or ("6042999") or ("6110648") or ("6174801") or ("6319815") or ("6436810") or ("6451620") or ("6455436") or ("6518669") or ("6613686") or ("6787474") or ("6815148") or ("6821687") or ("6833316") or ("6852619") or ("5906911") or ("6093508") or ("5821169") or ("6103616") or ("6150256") or ("6153521") or ("6184128") or ("6221759") or ("6221759") or ("6309955") or ("6355399") or ("6455416") or ("6479380") or ("6632707") or ("5877075") or ("5976968") or ("6063711") or ("6110826") or ("6180512") or ("6153514") or ("6156643") or ("6165899") or ("6174804") or ("6194326")).PN.	USPAT; USOCR	OR	OFF	2005/05/11 08:13
S41	62	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj (transmi$9 or shield$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:32
S42	27	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (light adj (transmi$9 or shield$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:53

S43	2737	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:18
S44	3	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (oversiz$4 and undersiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:53
S45	5	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (oversiz$4 and undersiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:52
S46	4	"438"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and (oversiz$4 and undersiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:51
S47	297	"438"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:21
S48	352	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:22
S49	478	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:21
S50	13	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj transmi$9) and (light adj shield$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:51

S51	0	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj transmi$9) and (light adj shield$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:22
S52	9	"438"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj transmi$9) and (light adj shield$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:50
S53	0	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj transmi$9) and (light adj shield$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:23
S54	5	"257"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj (transmi$9 or shield$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:50
S55	14	"438"/$.ccls. and (dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj (transmi$9 or shield$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:46
S56	29	(dual adj damascene) and @ad<="20030522" and semiconductor and (mask or resist or photoresist) and ((oversiz$4 and undersiz$4) or (overlap$5)) and (light adj (transmi$9 or shield$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 13:24
S68	1	semiconductor with (grind$6 adj10 back) with (plasma adj (etch$6 or lift-off)) with radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 12:22

S69	1	semiconductor with (grind$6 adj10 back) with (plasma adj (etch$6 or lift-off)) with (radiat$6 or irradiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 12:21
S70	1	semiconductor with (grind$6 adj10 back) with (plasma adj (etch$6 or lift-off)) with (ultraviolet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 12:21
S71	2	semiconductor same (grind$6 adj10 back) same (plasma adj (etch$6 or lift-off)) same radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 12:24
S72	0	semiconductor near (grind$6 adj10 back) near (plasma adj (etch$6 or lift-off)) near radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 12:22
S73	32	semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:17
S74	4	semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and (ultraviolet adj (radiat$6 or irradiat$6))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:13
S75	4	semiconductor and (grind$6 adj10 back) and (plasma adj etch$6) and (ultraviolet adj (radiat$6 or irradiat$6))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 12:24
S76	1694	(438/706).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:13

S77	2	438/706.ccls. and semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 13:14
S78	20	"438"/$.ccls. and semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 13:15
S79	22	"257"/$.ccls. and semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and radiat$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:24
S80	1	"257"/$.ccls. and semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and (adhesive with (harden or curing) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:25
S81	3	"438"/$.ccls. and semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and (adhesive with (harden or curing) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:25
S82	4	semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and (adhesive with (harden or curing) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:27
S83	5	(("6646289") or ("5801084") or ("5780311") or ("5530266") or ("4612408")).PN.	USPAT; USOCR	OR	OFF	2005/06/27 11:29
S84	4	semiconductor and (grind$6 adj10 back) and (plasma adj (etch$6 or lift-off)) and (adhesive with (harden or curing) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:29
S85	4	semiconductor and (grind$6 near back) and (plasma adj (etch$6 or lift-off)) and (adhesive with (harden or curing) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:29

S86	4	semiconductor and (grind$6 near back) and (plasma adj (etch$6 or lift-off)) and ((adhesive and (harden or curing)) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:30
S87	4	semiconductor and (grind$6 near back) and (plasma adj (etch$6 or lift-off)) and ((adhesive and (harden or harden$4 or curing)) with radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:36
S88	41	(semiconductor adj wafer) and tape and (grind$6) and (plasma adj (etch$6 or lift-off)) and ((adhesive and (harden or harden$4 or curing)) and radiat$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:37